UNISONIC TECHNOLOGIES CO., LTD

UTG50N120ND-S

Preliminary

Insulated Gate Bipolar Transistor

TO-247

1200V TRENCH GATE FIELD-STOP IGBT

■ DESCRIPTION

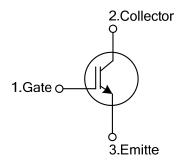
The UTC **UTG50N120ND-S** is an Trench Field-Stop Insulated Gate Bipolar Transistor. it uses UTC's advanced technology to provide customers with high switching speed, low saturation voltage and low switching loss, etc.

The UTC **UTG50N120ND-S** is suitable for the resonant or soft switching applications.

■ FEATURES

- * High switching speed
- * High avalanche ruggedness
- * Low saturation voltage: $V_{CE(SAT).Typ.}$ = 1.65V @ I_C =50A, V_{GE} =15V (T_C =25°C)

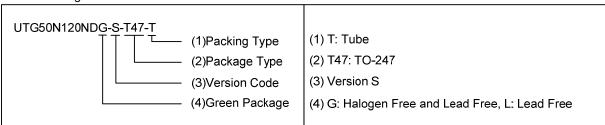
■ SYMBOL



ORDERING INFORMATION

Ordering Number		Daalaaaa	Pin Assignment			Da alaina	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UTG50N120NDL-S-T47-T	UTG50N120NDG-S-T47-T	TO-247	G	С	E	Tube	

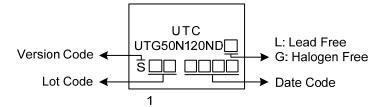
Note: Pin Assignment: G: Gate C: Collector E: Emitter



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■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT	
Collector-Emitter Voltage	V_{CES}	1200	V	
Gate-Emitter Voltage	\ <u>'</u>	±20	V	
Transient Gate-emitter voltage (tp < 5 ms)	V _{GES}	±25	V	
Continuous Collector Current		100	Α	
T _C =100°C	Ic	50	Α	
Collector Current Pulsed (Note 1)	I _{CM}	200	Α	
Short Circuit Withstand Time				
V _{GE} = 15V, V _{CC} ≤ 200V				
Allowed number of short circuits < 1000	t _{SC}	10	μs	
Time between short circuits: ≥1.0s				
$T_{\text{VJ}} = 25^{\circ}\text{C}$			ļ	
Power Dissipation (T _C =25°C)	P _D	285	W	
Operating Junction Temperature	T_J	-40 ~ +150	°C	
Storage Temperature Range	T _{STG}	-55 ~ +150	°C	

Notes: 1. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

Absolute maximum ratings are those values beyond which the device could be permanently damaged.

■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Case	θјс	0.44	°C/W

■ **ELECTRICAL CHARACTERISTICS** (Tc=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Collector-Emitter Breakdown Voltage	BV _{CES}			1200			V
Collector Cut-Off Current	Ices	V _{CE} =1200V, V _{GE} =0V				250	μΑ
G-E Leakage Current	I _{GES}	V _{CE} =0V, V _{GE} =±20V				±250	nA
On CHARACTERISTICS							
Gate to Emitter Threshold Voltage	$V_{GE(TH)}$	I _C =250μA, V _{CE} =V _{GE}		4.5		6.5	V
Collector to Emitter Saturation Voltage	V _{CE(SAT)}	Ic=50A, V _{GE} =15V	T _C =25°C		1.65	2.1	V
			T _C =125°C		2.0		V
DYNAMIC CHARACTERISTICS							
Input Capacitance	C _{IES}	V _{CE} =25V, V _{GE} =0V, f=1MHz			2510		pF
Output Capacitance	C_OES				156		pF
Reverse Transfer Capacitance	C _{RES}				47		pF
SWITCHING CHARACTERISTICS							
Turn-On Delay Time	t _{DON)}			22		ns	
Rise Time	t_R	V _{CC} =600V, I _C =50A, R _G =5Ω, V _{GE} =0~15V, L=500μH			100		ns
Turn-Off Delay Time	t _{DOFF)}				139		ns
Fall Time	t _F				181		ns
Turn-On Switching Loss	Eon			6.79		mJ	
Turn-Off Switching Loss	E _{OFF}]			4.93		mJ

^{2.} Pulse width limited by maximum junction temperature.

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